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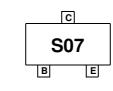


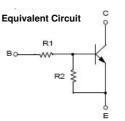
# **FJY3007R NPN Epitaxial Silicon Transistor**

# **Features**

- · Switching circuit, Inverter, Interface circuit, Driver Circuit
- Built in bias Resistor (R1=22KΩ, R2=47KΩ)
- Complement to FJY4007R







## Absolute Maximum Ratings \* T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	50	V
V <sub>CEO</sub>	Collector-Emitter Voltage	50	V
V <sub>EBO</sub>	Emitter-Base Voltage	10	V
I <sub>C</sub>	Collector Current	100	mA
T <sub>STG</sub>	Storage Temperature Range	-55~150	٥C
TJ	Junction Temperature	150	٥°
P <sub>C</sub>	Collector Power Dissipation, by $R_{\theta JA}$	200	mW

These ratings are limiting values above which the serviceability of any semiconductor device may by impaired.

#### Thermal Characteristics\* Ta=25°C unless otherwise noted

Symbol	Parameter	Мах	Units
$R_{\thetaJA}$	Thermal Resistance, Junction to Ambient	600	°C/W

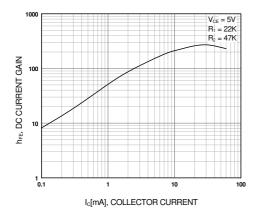
\* Minimum land pad size.

### Electrical Characteristics\* T<sub>c</sub> = 25°C unless otherwise noted

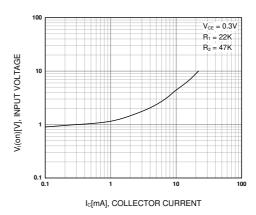
Parameter	Test Condition	MIN	Тур	MAX	Units
Collector-Emitter Breakdown Voltage	Ic = 10 uA, IE = 0	50			V
Collector-Base Breakdown Voltage	Ic = 100 uA, I <sub>B</sub> = 0	50			V
Collector-Cutoff Current	$V_{CB} = 40 V, I_{E} = 0$			0.1	uA
DC Current Gain	Vce = 5 V, Ic = 5 mA	68			
Collector-Emitter Saturation Voltage	Ic = 10 mA, I <sub>B</sub> = 0.5 mA			0.3	V
Current Gain - Bandwidth Product	Vce = 10V, Ic = 5 mA		250		MHz
Output Capacitance	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1.0 MHz		3.7		pF
Input Off Voltage	Vce = 5 V, Ic = 100uA	0.4			V
Input On Voltage	$V_{CE} = 0.3V$ , $I_C = 2mA$			2.5	V
Input Resistor		15	22	29	KΩ
Resistor Ratio		0.42	0.47	0.52	
	Collector-Emitter Breakdown Voltage Collector-Base Breakdown Voltage Collector-Cutoff Current DC Current Gain Collector-Emitter Saturation Voltage Current Gain - Bandwidth Product Output Capacitance Input Off Voltage Input Off Voltage Input Nover Collector	Collector-Emitter Breakdown VoltageIc = 10 uA, IE = 0Collector-Base Breakdown VoltageIc = 100 uA, IB = 0Collector-Cutoff CurrentVcB = 40 V, IE = 0DC Current GainVcE = 5 V, Ic = 5 mACollector-Emitter Saturation VoltageIc = 10 mA, IB = 0.5 mACurrent Gain - Bandwidth ProductVcE = 10V, Ic = 5 mAOutput CapacitanceVcB = 10 V, IE = 0, f = 1.0 MHzInput Off VoltageVcE = 5 V, Ic = 100uAInput On VoltageVcE = 0.3V, Ic = 2mAInput ResistorVcE = 0.3V, Ic = 2mA	Collector-Emitter Breakdown VoltageIc = 10 uA, IE = 050Collector-Base Breakdown VoltageIc = 100 uA, IE = 050Collector-Cutoff CurrentVcB = 40 V, IE = 050DC Current GainVcE = 5 V, Ic = 5 mA68Collector-Emitter Saturation VoltageIc = 10 mA, IB = 0.5 mA68Current Gain - Bandwidth ProductVcE = 10V, Ic = 5 mA0Output CapacitanceVcB = 10 V, Ic = 5 mA0.4Input Off VoltageVcE = 5 V, Ic = 100uA0.4Input On VoltageVcE = 0.3V, Ic = 2mA15	Collector-Emitter Breakdown VoltageIc = 10 uA, IE = 050Collector-Base Breakdown VoltageIc = 100 uA, IB = 050Collector-Cutoff CurrentVcB = 40 V, IE = 00DC Current GainVcE = 5 V, Ic = 5 mA68Collector-Emitter Saturation VoltageIc = 10 mA, IB = 0.5 mA68Current Gain - Bandwidth ProductVcE = 10V, Ic = 5 mA250Output CapacitanceVcB = 10 V, IE = 0, f = 1.0 MHz3.7Input Off VoltageVcE = 5 V, Ic = 100uA0.4Input On VoltageVcE = 0.3V, Ic = 2mA15	Collector-Emitter Breakdown VoltageIc = 10 uA, IE = 050Collector-Base Breakdown VoltageIc = 100 uA, IB = 050Collector-Cutoff CurrentVcB = 40 V, IE = 00.1DC Current GainVcE = 5 V, Ic = 5 mA68Collector-Emitter Saturation VoltageIc = 10 mA, IB = 0.5 mA0.3Current Gain - Bandwidth ProductVcE = 10V, Ic = 5 mA250Output CapacitanceVcB = 10 V, IE = 0, f = 1.0 MHz3.7Input Off VoltageVcE = 5 V, Ic = 100uA0.4Input On VoltageVcE = 0.3V, Ic = 2mA2.5Input Resistor152229

# **Typical Performance Characteristics**

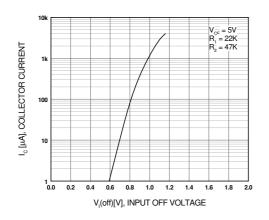
#### Figure 1. DC current Gain



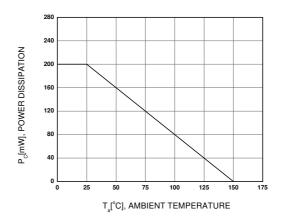
### Figure 2. Input On Voltage

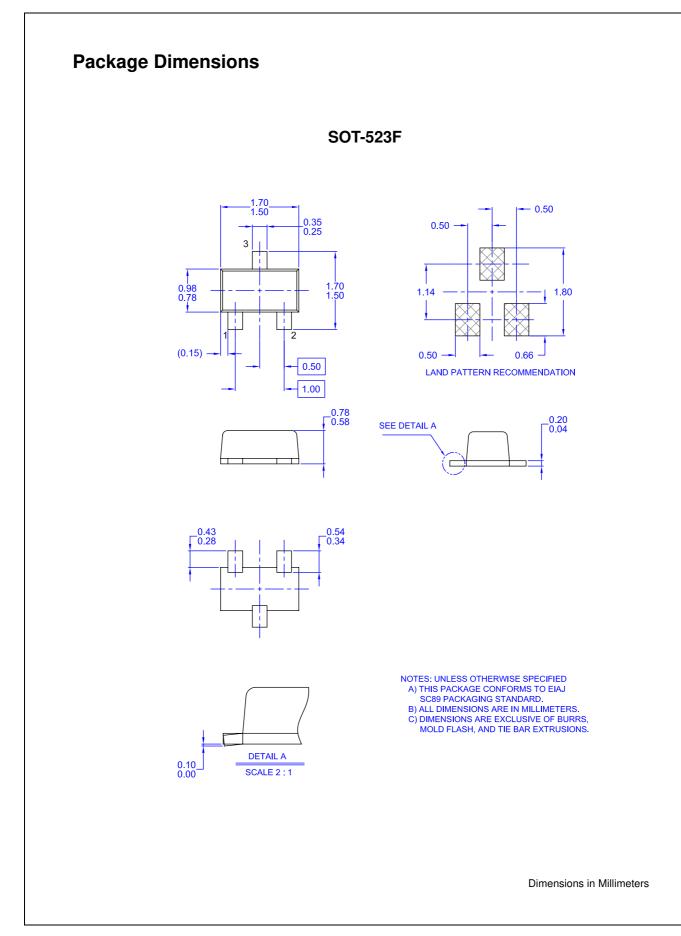


#### Figure 3. Input off Voltage



#### Figure 4. Power Derating





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